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PTO/SB/21 (09-04)
Approved for use through 07/31/2006. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

(E JO	Application Number	10/643,680						
(P TRANSMITTAL	Filing Date	August 18, 2003						
NOV 17 2004 E FORM	First Named Inventor	Brenda D. Kraus						
NOV 1	Art Unit	1762						
(to be used for all correspondence after initial i	Examiner Name	Unknown						
TENT &	Attorney Docket Number	MI22-2310						
Total Number of Pages in This Submission								
	ENCLOSURES (Check all that apply)							
Fee Transmittal Form	Drawing(s)	After Allowance Communication to TC						
Fee Attached	Licensing-related Papers	Appeal Communication to Board of Appeals and Interferences						
Amendment/Reply	Petition Petition to Convert to a	Appeal Communication to TC (Appeal Notice, Brief, Reply Brief)						
After Final	Provisional Application	Proprietary Information						
Affidavits/declaration(s)	Power of Attorney, Revocation Change of Correspondence Ad	ddress Status Letter						
Extension of Time Request	Terminal Disclaimer	Other Enclosure(s) (please Identify below):						
Express Abandonment Request	Request for Refund	Return Receipt Postcard , PTO-1449 , Cited References						
X Information Disclosure Statement	CD, Number of CD(s)							
Information Biodiosaro Gatemani	Landscape Table on CD							
Certified Copy of Priority Document(s)	Remarks							
Reply to Missing Parts/	Customer No. 021567							
Incomplete Application	No fee is required with this filing. However, should a fee be determined as owing, charge such fee to							
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Mark S. Matkin	7 /al/	Reg. No. 22 200						
Date ////	1107	32,268						
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

<i>₹</i> / .	
Patent Application Serial No.	
Filing Date	August 18, 2003
Inventorship	Brenda D. Kraus et al.
Assignee	Micron Technology, Inc.
Group Art Unit	
Examiner	Unknown
Attorney's Docket No	
Title: Atomic Layer Deposition Methods of	of Forming Conductive Metal Nitride
Comprising Layers	

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S. patents or U.S. patent application publications are included, as the date of filing of this patent application occurs after June 30, 2003. No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing of a first Office Action on the merits, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 11-17-04

Mark S. Matkin Reg. No. 32,268

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Form	PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY, DOCKET NO. MI22-2310

SERIAL NO. 10/643,680

IST OF ART CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT: Kraus et al.

FILING DATE August 18, 2003

GROUP 1762

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*	AJ			04/2001				Yes	No	
	AK			0 1/2001						
	AL								<u> </u>	
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EXAMINER	EXAMINER DATE CONSIDERED									

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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